2SA1908

Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC5100)

Application : Audio and General Purpose

■Absolute maximum ratings (Ta=25°C)

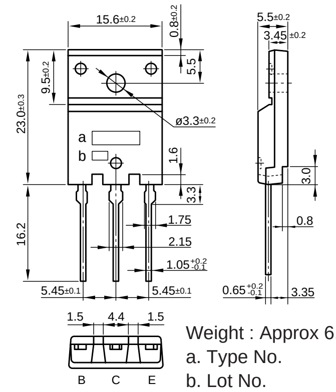
Symbol	2SA1908	Unit
V_{CBO}	–120	V
V_{CEO}	–120	V
V_{EBO}	–6	V
I_C	–8	A
I_B	–3	A
P_C	75(Tc=25°C)	W
Tj	150	°C
Tstg	–55 to +150	°C

■Electrical Characteristics (Ta=25°C)

Symbol	Conditions	2SA1908	Unit
I_{CBO}	V_{CB}=–120V	–10max	μA
I_{EBO}	V_{EB}=–6V	–10max	μA
$V_{(BR)CEO}$	I_C=–50mA	–120min	V
h_{FE}	V_{CE}=–4V, I_C=–3A	50min*	
$V_{CE}(sat)$	I_C=–3A, I_B=–0.3A	–0.5max	V
f_T	V_{CE}=–12V, I_E=0.5A	20typ	MHz
C_{OB}	V_{CB}=–10V, f=1MHz	300typ	pF

*h_{FE} Rank O(50 to 100), P(70 to 140), Y(90 to 180)

External Dimensions FM100(TO3PF)

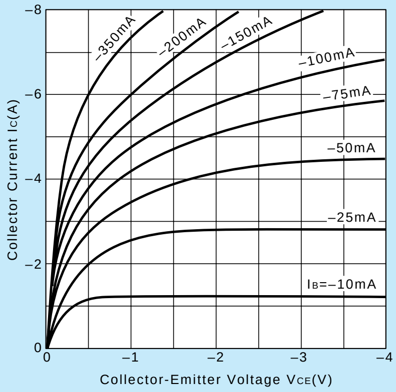


Weight : Approx 6.5g
a. Type No.
b. Lot No.

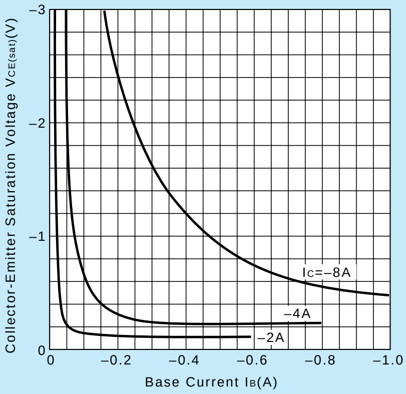
■Typical Switching Characteristics (Common Emitter)

V_{CC} (V)	R_L (Ω)	I_C (A)	V_{BB1} (V)	V_{BB2} (V)	I_{B1} (A)	I_{B2} (A)	ton (μs)	tstg (μs)	tf (μs)
–40	10	–4	–10	5	–0.4	0.4	0.14typ	1.40typ	0.21typ

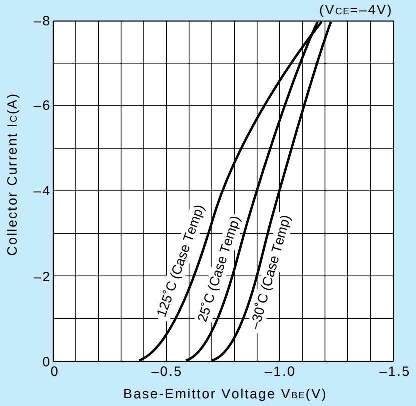
I_C–V_{CE} Characteristics (Typical)



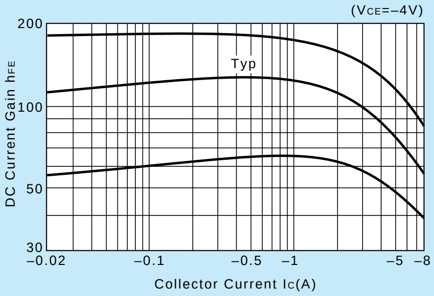
V_{CE}(sat)–I_B Characteristics (Typical)



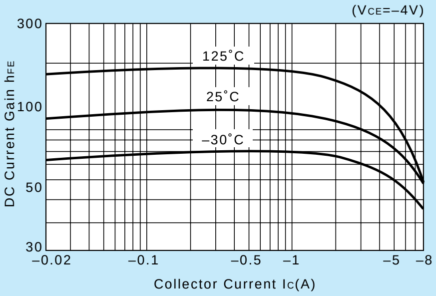
I_C–V_{BE} Temperature Characteristics (Typical)



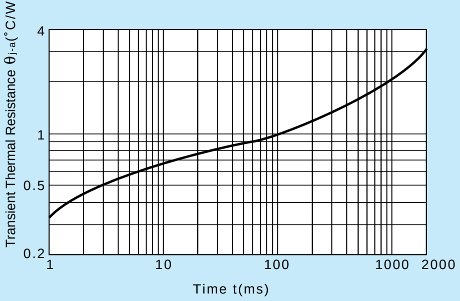
h_{FE}–I_C Characteristics (Typical)



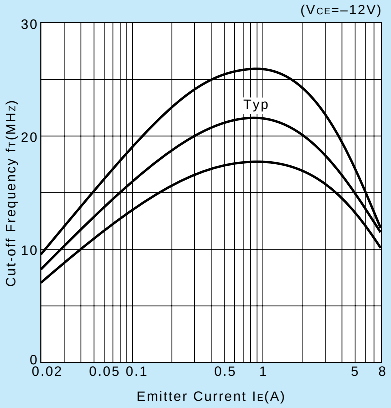
h_{FE}–I_C Temperature Characteristics (Typical)



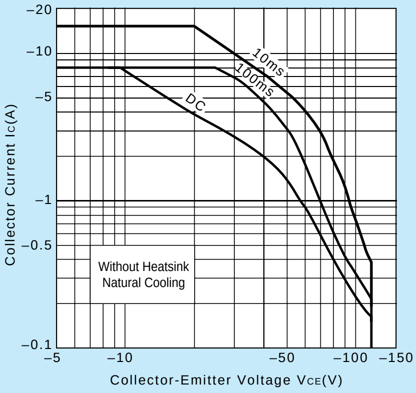
$\theta_{j\text{-}a}$–t Characteristics



f_T–I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



P_C–Ta Derating